

MJ N-Channel Enhancement Mode Power MOSFET

Description

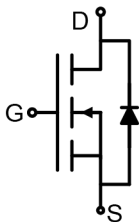
The MJ3055 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a Battery protection or in other Switching application.

General Features

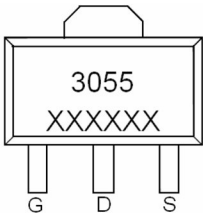
- ◆ $V_{DS} = 60V, I_D = 3.0A$
 $R_{DS(ON)} < 100m\Omega @ V_{GS} = 10V$
 $R_{DS(ON)} < 120m\Omega @ V_{GS} = 4.5V$
- ◆ High power and current handing capability
- ◆ Lead free product is acquired
- ◆ Surface Mount Package

Application

- ◆ Battery switch
- ◆ DC/DC converter



Schematic diagram



SOT-89 -3L top view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
3055	MJ3055	SOT-89-3L	Ø180mm	12mm	1000 units

Absolute Maximum Ratings (Tc =25 °Cunless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V_{DS}	60	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	3	A
Pulsed Drain Current ^(Note 1)	I_{DM}	10	A
Maximum Power Dissipation	P_D	1.7	W
Operating Junction and Storage Temperature Range	T_J, T_{STG}	-55 To 150	°C

Thermal Characteristic

Thermal Resistance,Junction-to-Ambient ^(Note 2)	$R_{\theta JA}$	73.5	°C/W
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Electrical Characteristics (T_A =25℃unless otherwise noted)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =250μA	60	65	-	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V,V _{GS} =0V	-	-	1	μA
Gate-Body Leakage Current	I _{GSS}	V _{DS} =±20V,V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} ,I _D =250μA	1.0	1.3	2.0	V
Drain-Source On-State Resistance	R _{DS(ON)}	V _{GS} =10V, I _D =3A	-	73	100	mΩ
		V _{GS} =4.5V, I _D =3A	-	90	120	mΩ
Forward Transconductance	g _{FS}	V _{DS} =15V,I _D =2A	2	-	-	S
Dynamic Characteristics ^(Note 4)						
Input Capacitance	C _{iss}	V _{DS} =30V,V _{GS} =0V, F=1.0MHz	-	247	-	PF
Output Capacitance	C _{oss}		-	34	-	PF
Reverse Transfer Capacitance	C _{rss}		-	19.5	-	PF
Switching Characteristics ^(Note 4)						
Turn-on Delay Time	t _{d(on)}	V _{DD} =30V, ,I _D =1.5A V _{GS} =10V,R _{GEN} =1Ω	-	6	-	nS
Turn-on Rise Time	t _r		-	15	-	nS
Turn-Off Delay Time	t _{d(off)}		-	15	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Q _g	V _{DS} =30V,I _D =3A, V _{GS} =4.5V	-	6	-	nC
Gate-Source Charge	Q _{gs}		-	1	-	nC
Gate-Drain Charge	Q _{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ^(Note 3)	V _{SD}	V _{GS} =0V,I _S =3A	-	-	1.2	V
Diode Forward Current ^(Note 2)	I _S		-	-	3	A

Notes:

- ① Repetitive Rating: Pulse width limited by maximum junction temperature.
② Surface Mounted on FR4 Board, t ≤ 10 sec.
③ Pulse Test: Pulse Width ≤ 300μs, Duty Cycle ≤ 2%.
④ Guaranteed by design, not subject to production

Typical Electrical and Thermal Characteristics

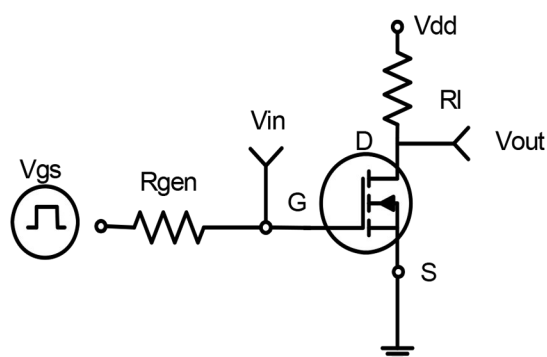


Figure 1 Switching Test Circuit

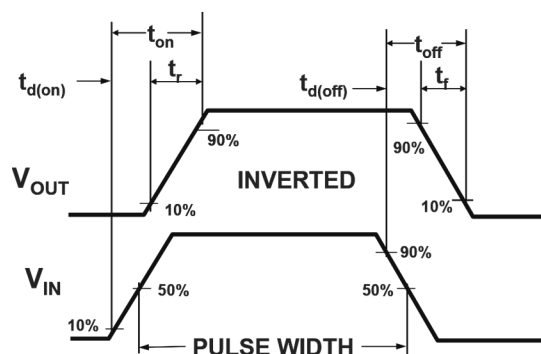


Figure 2 Switching Waveforms

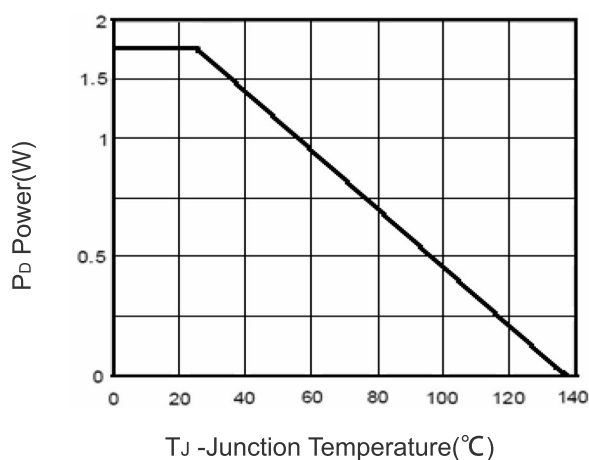


Figure 3 Power Dissipation

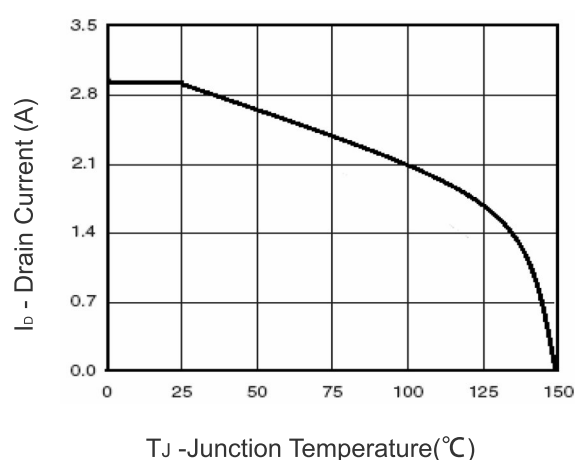


Figure 4 Drain Current

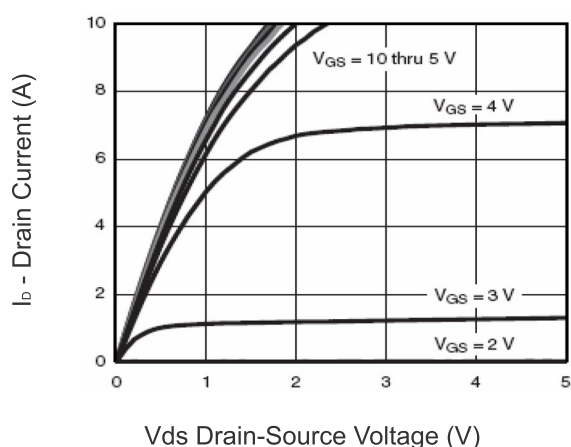


Figure 5 Output Characteristics

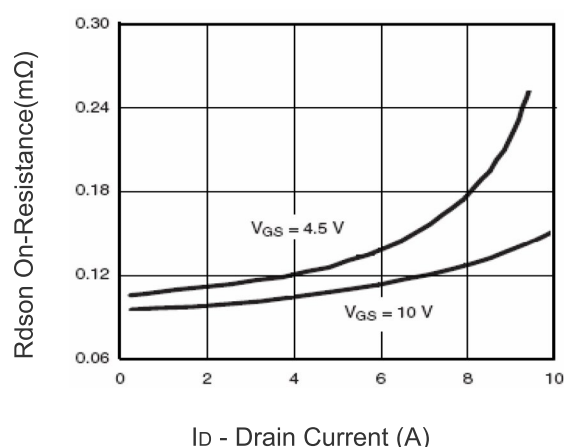
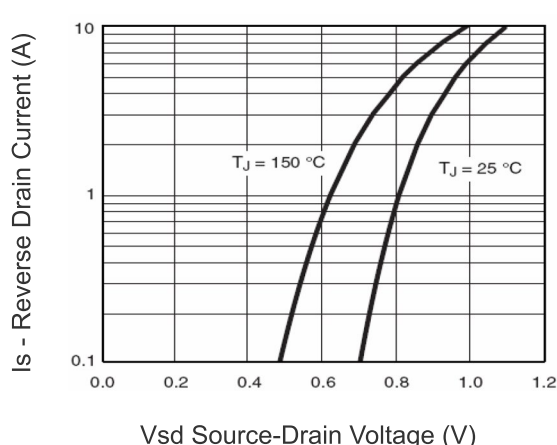
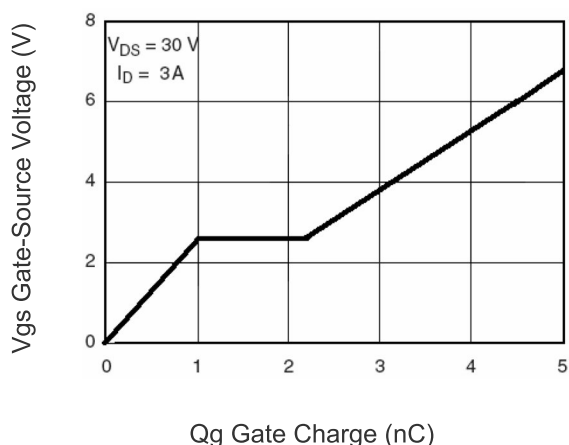
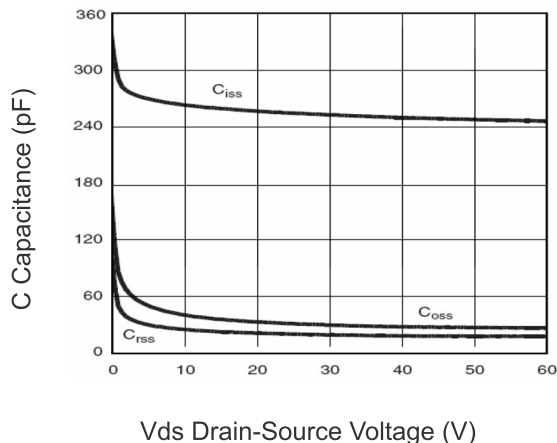
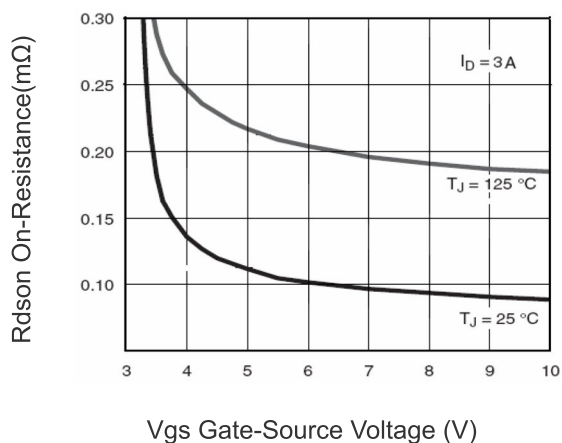
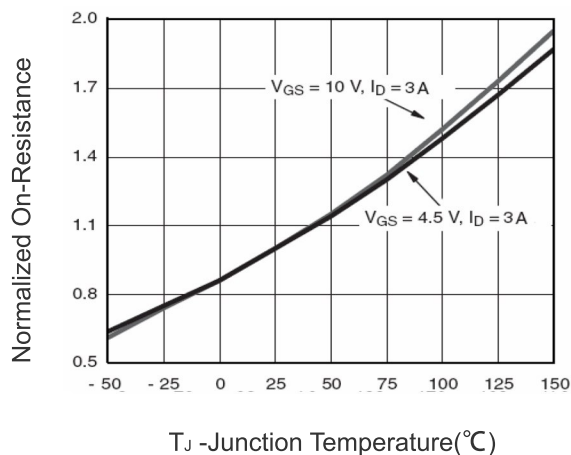
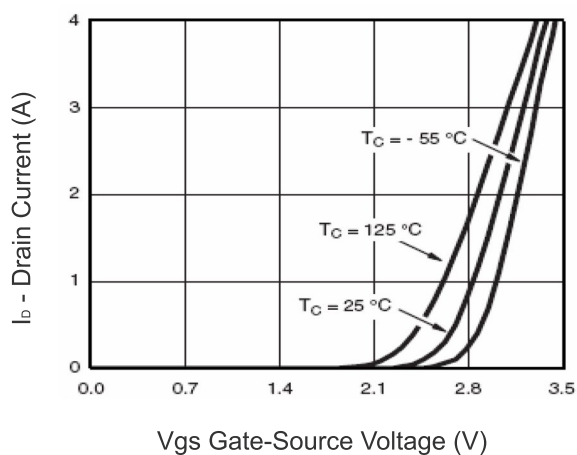


Figure 6 Drain-Source On-Resistance



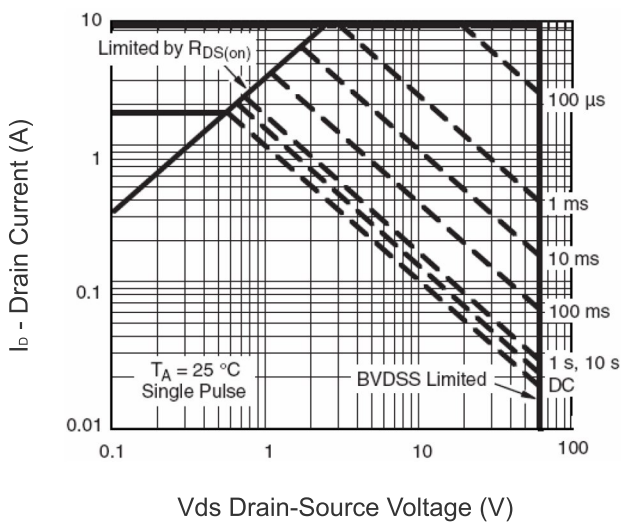


Figure 13 Safe Operation Area

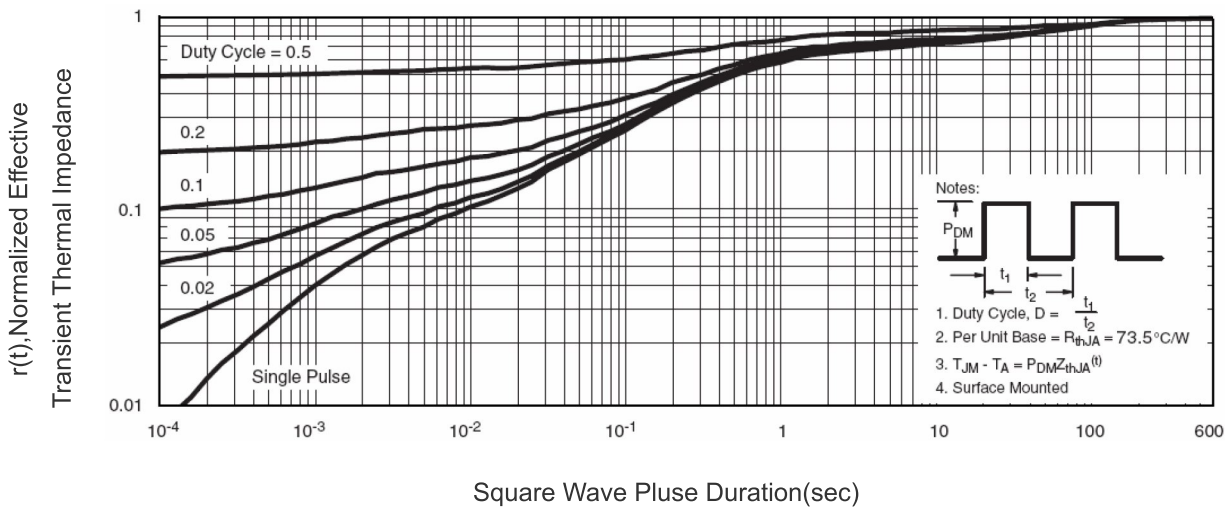
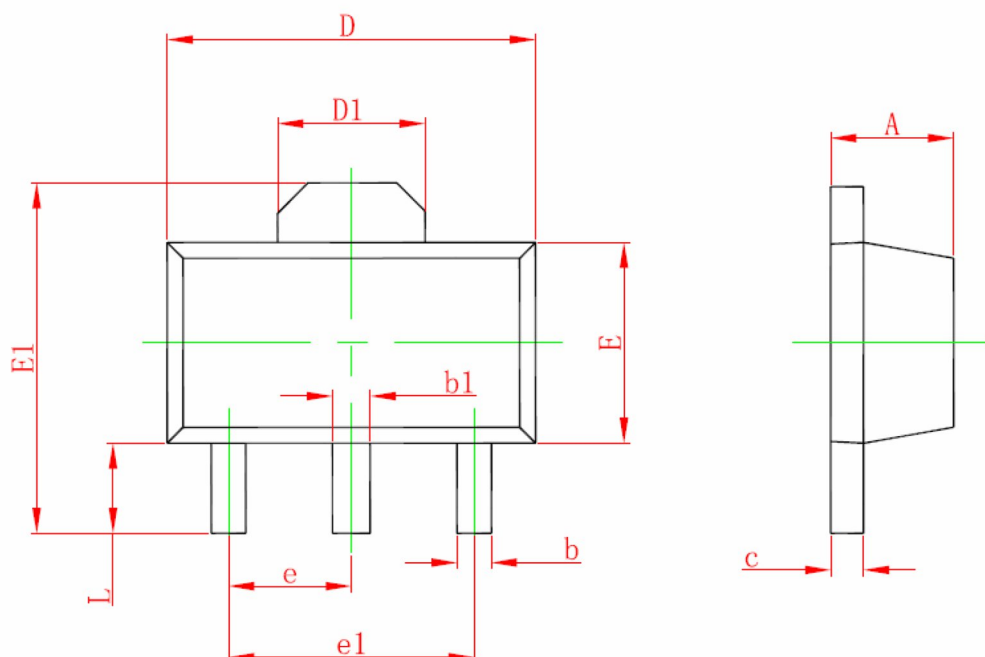


Figure 14 Normalized Maximum Transient Thermal Impedance

SOT-89-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.400	1.600	0.055	0.063
b	0.320	0.520	0.013	0.020
b1	0.400	0.580	0.016	0.023
c	0.350	0.440	0.014	0.017
D	4.400	4.600	0.173	0.181
D1	1.550 REF.		0.061 REF.	
E	2.300	2.600	0.091	0.102
E1	3.940	4.250	0.155	0.167
e	1.500 TYP.		0.060 TYP.	
e1	3.000 TYP.		0.118 TYP.	
L	0.900	1.200	0.035	0.047

Notes:

- ① All dimensions are in millimeters.
- ② Tolerance $\pm 0.10\text{mm}$ (4 mil) unless otherwise specified
- ③ Package body sizes exclude mold flash and gate burrs. Mold flash at the non-lead sides should be less than 5 mils.
- ④ Dimension L is measured in gauge plane.
- ⑤ Controlling dimension is millimeter, converted inch dimensions are not necessarily exact.

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